

**AMENDMENTS TO THE CLAIMS**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**LISTING OF CLAIMS:**

Claim 1 (currently amended): A liquid crystal display device comprising:

a transistor including:

a source electrode and a drain electrode arranged in mutually opposing relation;

a semiconductor film comprising at least one layer disposed between the source electrode and the drain electrode;

a gate electrode disposed in adjacent relation to the semiconductor film; and

a gate insulating film disposed between the gate electrode and each of the source electrode, the drain electrode, and the semiconductor film; wherein

a concentration of fluorine contained in the gate insulating film is in a range of about  $7 \times 10^{18}$  atoms/cm<sup>3</sup> to about  $1 \times 10^{20}$  atoms/cm<sup>3</sup>;

the transistor is of an inverted stagger type in which the gate insulating film and the semiconductor film are formed in that order and the semiconductor film is disposed on the gate insulating film; and

the gate insulating film is an amorphous silicon nitride film; ~~and~~

~~the transistor defines a switching element for a pixel electrode portion.~~

Claim 2 (previously amended): The liquid crystal display device of claim 1, wherein the concentration of the contained fluorine is in a range of about  $7 \times 10^{18}$  atoms/cm<sup>3</sup> to about  $1 \times 10^{19}$  atoms/cm<sup>3</sup>.

Claim 3 (previously amended): The liquid crystal display device of claim 1, wherein the transistor is of a field-effect type.

Claim 4 (canceled).

Claim 5 (previously amended): The liquid crystal display device of claim 1, wherein the gate insulating film is deposited by a CVD method.

Claims 6-8 (canceled).